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| INFORMATION DISCLOSURE<br>STATEMENT BY APPLICANT<br>(Use as many sheets as necessary) |   |    | Complete if Known    |                        |               |
|   |   |    | Application Number   | 10/671,233-Conf. #8199 |               |
|   |   |    | Filing Date          | September 25, 2003     |               |
|   |   |    | First Named Inventor | Jian H. Zhao           |               |
|   |   |    | Art Unit             | 2826                   |               |
|   |   |    | Examiner Name        | T. N. Tran             |               |
| Sheet   | 1 | of | 1                    | Attorney Docket Number | OCIRS 3.0-088 |

| U.S. PATENT DOCUMENTS |                       |  |                                |  |   |
|-----------------------|-----------------------|--|--------------------------------|--|---|
| Examiner Initials*    | Cite No. <sup>1</sup> | Document Number                          | Publication Date<br>MM-DD-YYYY | Name of Patentee or<br>Applicant of Cited Document | Pages, Columns, Lines, Where<br>Relevant Passages or Relevant<br>Figures Appear |
|                       |                       | Number-Kind Code <sup>2</sup> (if known) |                                |  |   |
| TT                    | AA                    | US-6,107,649                             | 08-22-2000                     | Jian H. Zhao                                       | Column 1, Figure 6A   |
| TT                    | AB                    | US-5,903,020                             | 05-11-99                       | Richard R. Siergiej, et al.                        | Fig. 3, Fig. 5, Fig. 10   |

| FOREIGN PATENT DOCUMENTS |                       |   |                  |   |   |                |
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| Examiner Initials*       | Cite No. <sup>1</sup> | Foreign Patent Document   | Publication Date | Name of Patentee or Applicant of Cited Document | Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear | T <sup>3</sup> |
|                          |                       | Country Code <sup>4</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup> (if known) | MM-DD-YYYY       |   |   |                |
|                          |                       |   |                  |   |   |                |

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| NON PATENT LITERATURE DOCUMENTS |                       |   |                |
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| Examiner Initials               | Cite No. <sup>1</sup> | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published. | T <sup>2</sup> |
| TT                              | CC                    | K. ASANO, et. al, 5kV 4H-SiC SEJFET with Low RonS of 69 m-ohm-cm2, Proc. of 14 <sup>th</sup> Intl. Symp. on Power Semiconductor Devices & IC 2002, June 3, 2002, pp. 61-64, IEEE, Piscataway, NJ, USA.  |                |
| TT                              | CD                    | J. Nishizawa, et. al., The 2.45 GHz 35 W CW SI recessed gate type SIT with high gain and high voltage operation, IEEE Trans. on Electron Devices, Feb. 2000, pp. 482-487, Vol. 4, No. 2, IEEE, Piscataway, NJ, USA  |                |
| TT                              | CE                    | H. Onose, et. al., 2KV 4H-SiC junction FETs, Materials Science Forum, 2002, pp. 1227-1230, Vols. 389-393, Trans Tech Publications, Switzerland  |                |
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| TT                              | CG                    | Jian H. Zhao, et al., Demonstration of a high performance 4H-SiC vertical junction field effect transistor without epitaxial regrowth, Feb. 2003, pp. 321-323, Electronics Letters, IEE, Stevenage, SG1 2SD, UK.  |                |

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|--------------------|------------|-----------------|------------|
| Examiner Signature | /Tan Tran/ | Date Considered | 09/21/2006 |
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